

L Number	Hits	Search Text	DB	Time stamp
1	3387	257/69.ccls. 257/517.ccls. 257/526.ccls. 257/774.ccls. 257/797.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/09/01 12:37
-	0	"perfect alignment" with "semiconductor mask"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:39
-	0	"perfect alignment" same "semiconductor mask"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:39
-	2	"perfect alignment" and "semiconductor mask"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:40
-	209	"shallow isolation trenches"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:40
-	59	"deep isolation trenches"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:40
-	9	"shallow isolation trenches" and "deep isolation trenches"	USPAT; US-PGPUB; EPO; JPO	2004/09/01 09:40
-	6	("shallow isolation trenches" and "deep isolation trenches") and align\$4	USPAT; US-PGPUB; EPO; JPO	2004/09/01 12:34